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PUB-NO: JP407263669A
DOCUMENT-IDENTIFIER: JP 07263669 A
TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

PUBN-DATE: October 13, 1995

INVENTOR-INFORMATION: COUNTRY

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APPL-NO: JP06056155
APPL-DATE: March 25, 1994

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ABSTRACT:

PURPOSE: To provide a semiconductor device having an anode-short structure wherein
irregularity of the ON-voltage and the turn-off time is improved and
mass-productivity is excellent, and its manufacturing method.

CONSTITUTION: A P-type base region 2, an N-type source region 3, a gate electrode
7 and a source electrode 9 are formed on one main surface of an N-type
semiconductor substrate 1 which turns to a drain region, and a P-type anode region
4 is formed on the other main surface of the semiconductor substrate 1. A trench
is dug so as to perfectly isolate the anode region 4, and an N-type
short-circuit region 5 is formed so as to fill the trench. Thereby an anode-short
structure is formed.

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2	BRS	L2	4265	1 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/04/22 12:53
3	BRS	L3	41	2 and (anode adj short)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/04/22 12:54

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